TENTATIVE TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (π-MOSV)

2SK2992

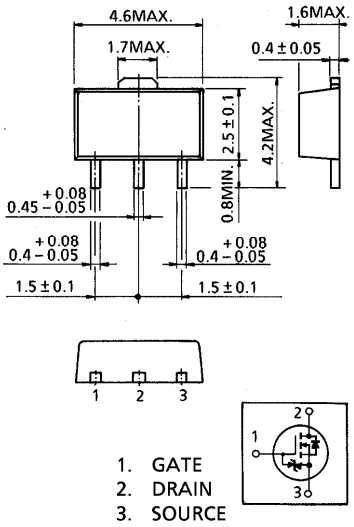
HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS

CHOPPER REGULATOR, DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

INDUSTRIAL APPLICATIONS

- Low Drain-Source ON Resistance : $R_{DS\ (ON)} = 2.2\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 0.9S$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100\mu A$ (Max.) ($V_{DS} = 200V$)
- Enhancement-Mode : $V_{th} = 2.0 \sim 3.5V$ ($V_{DS} = 10V$, $I_D = 1mA$)

Unit in mm



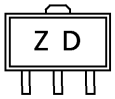
JEDEC	—
EIAJ	SC-62
TOSHIBA	2-5K1B

Weight : 0.05g (Typ.)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	200	V
Drain-Gate Voltage ($R_{GS} = 20k\Omega$)		V_{DGR}	200	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current	DC	I_D	1	A
	Pulse	I_{DP}	3	A
Drain Power Dissipation***		P_D	1.5	W
Single Pulse Avalanche Energy**		E_{AS}	36	mJ
Avalanche Current		I_{AR}	1	A
Repetitive Avalanche Energy*		E_{AR}	0.15	mJ
Channel Temperature		T_{ch}	150	°C
Storage Temperature Range		T_{stg}	−55~150	°C

MARKING



THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Ambient	$R_{th\ (ch-a)}$	250	°C / W

Note ;

* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

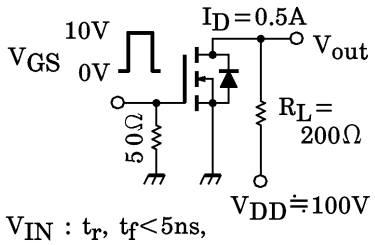
** $V_{DD} = 50V$, Starting $T_{ch} = 25°C$, $L = 56.7mH$, $R_G = 25\Omega$, $I_{AR} = 1A$

*** Mounted on ceramic substrate ($1inch^2 \times 0.8t$)

This transistor is an electrostatic sensitive device.
Please handle with caution.

961001EAA1

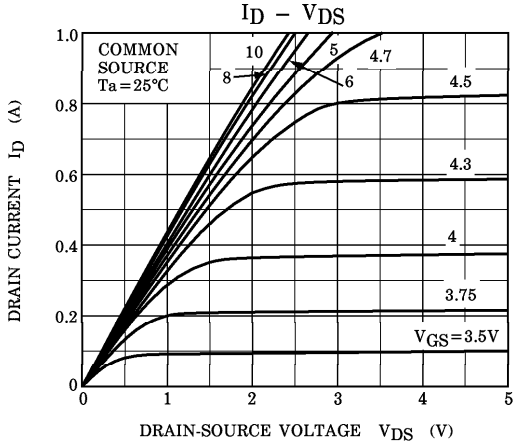
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	$V_{GS}=\pm16V$, $V_{DS}=0V$	—	—	±10	μA
Drain Cut-off Current		I_{DSS}	$V_{DS}=200V$, $V_{GS}=0V$	—	—	100	μA
Drain-Source Breakdown Voltage		$V_{(BR)\,DSS}$	$I_D=10mA$, $V_{GS}=0V$	200	—	—	V
Gate Threshold Voltage		V_{th}	$V_{DS}=10V$, $I_D=1mA$	2.0	—	3.5	V
Drain-Source ON Resistance		$R_{DS\,(ON)}$	$V_{GS}=10V$, $I_D=0.5A$	—	2.2	3.5	Ω
Forward Transfer Admittance		$\|Y_{fs}\|$	$V_{DS}=10V$, $I_D=0.5A$	0.5	0.9	—	S
Input Capacitance		C_{iss}	$V_{DS}=10V$, $V_{GS}=0V$ f = 1MHz	—	90	—	pF
Reverse Transfer Capacitance		C_{rss}		—	10	—	
Output Capacitance		C_{oss}		—	30	—	
Switching Time	Rise Time	t_r	 V_{IN} : t_r, $t_f<5ns$, Duty ≦ 1%, $t_w=10\mu s$	—	9	—	ns
	Turn-on Time	t_{on}		—	17	—	
	Fall Time	t_f		—	16	—	
	Turn-off Time	t_{off}		—	45	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q_g	$V_{DD}\fallingdotseq160V$, $V_{GS}=10V$ $I_D=1A$	—	3.0	—	nC
Gate-Source Charge		Q_{gs}		—	1.8	—	
Gate-Drain ("Miller") Charge		Q_{gd}		—	1.2	—	

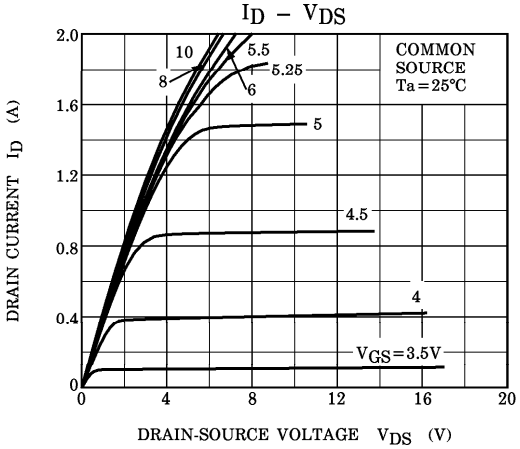
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	1	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	3	A
Diode Forward Voltage	V_{DSF}	$I_{DR}=1A$, $V_{GS}=0V$	—	—	−1.5	V
Reverse Recovery Time	t_{rr}	$I_{DR}=1A$, $V_{GS}=0V$	—	85	—	ns
Reverse Recovery Charge	Q_{rr}	$dI_{DR}/dt=100A/\mu s$	—	190	—	nC

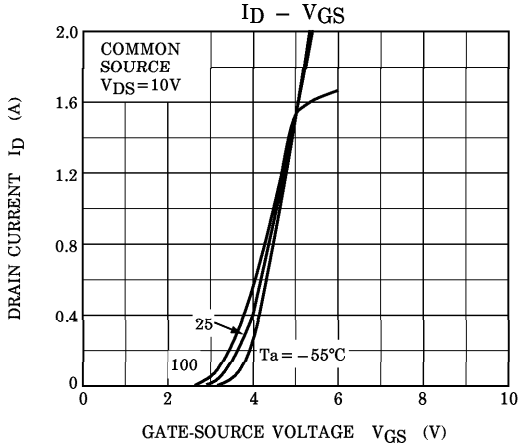
I_D – V_{DS}



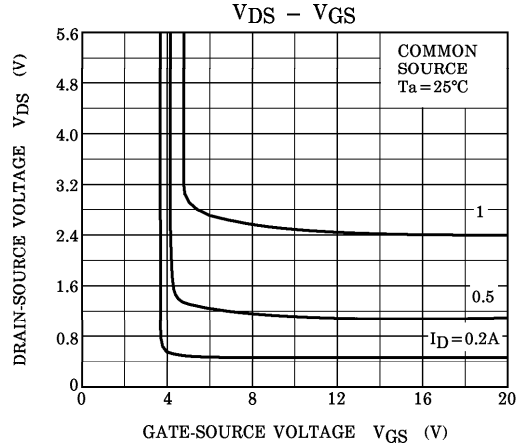
I_D – V_{DS}



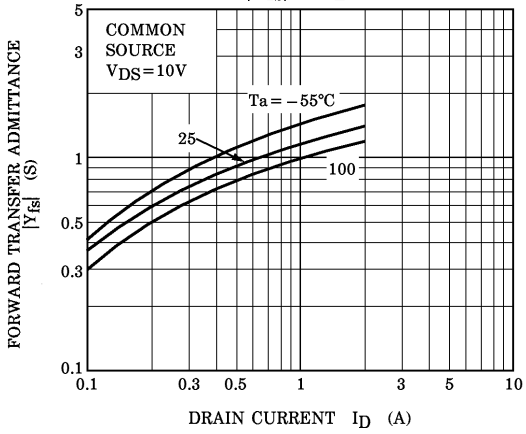
I_D – V_{GS}



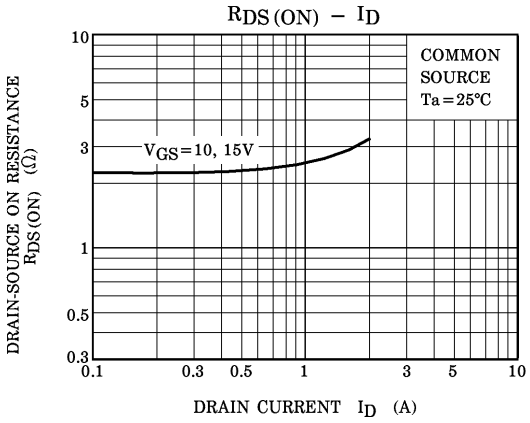
V_{DS} – V_{GS}



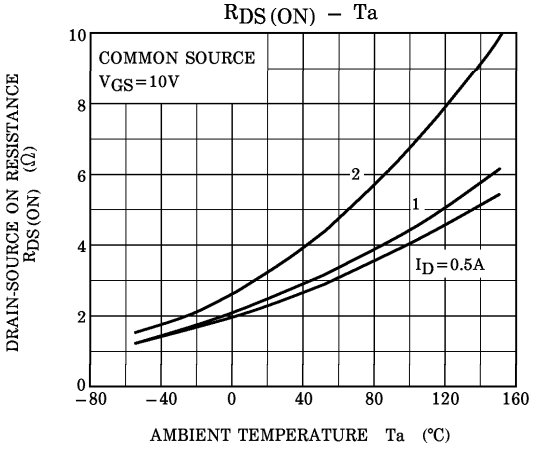
$|Y_{fs}|$ – I_D



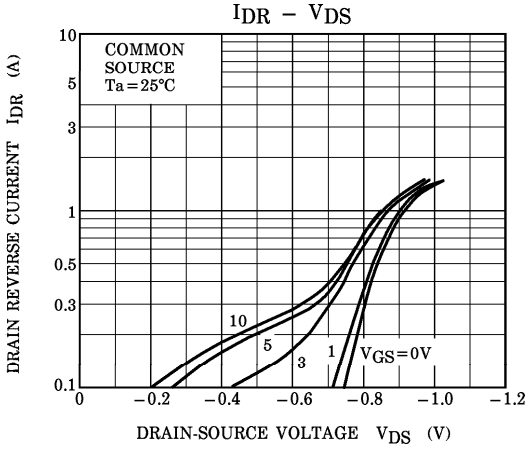
$R_{DS(ON)}$ – I_D



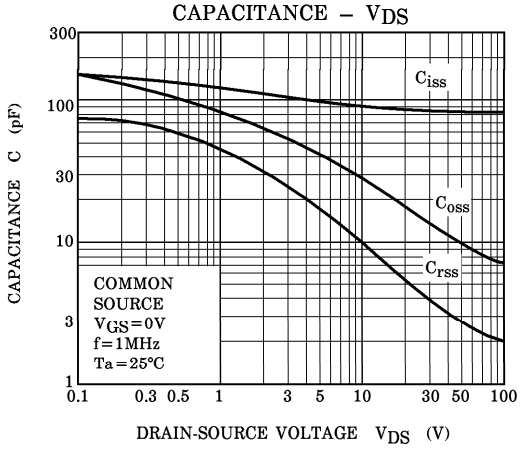
$R_{DS\,(ON)}$ – Ta



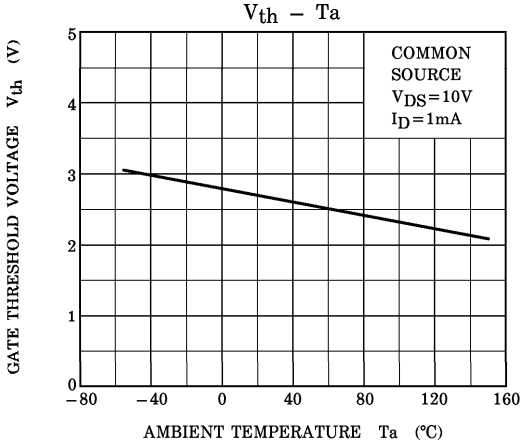
I_{DR} – V_{DS}



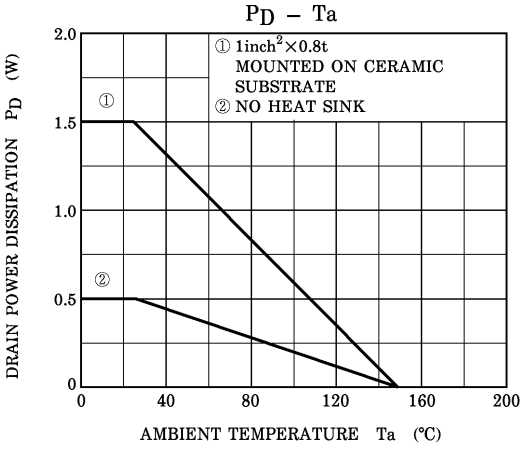
CAPACITANCE – V_{DS}



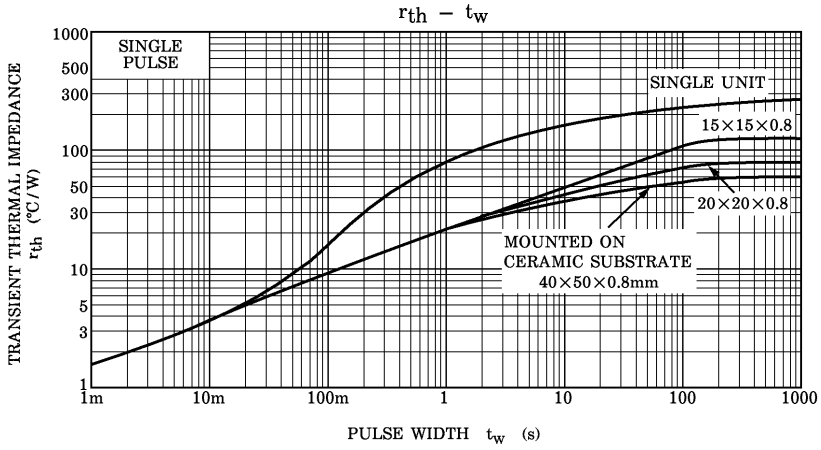
V_{th} – Ta



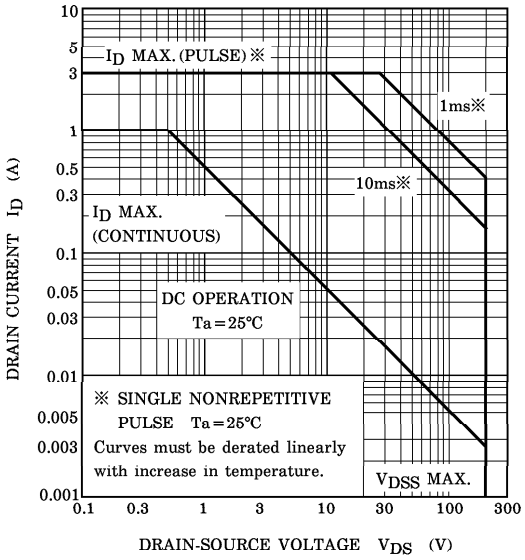
P_D – Ta



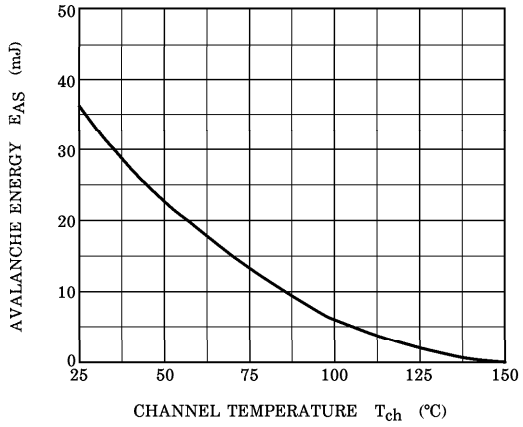
$r_{th} - t_w$

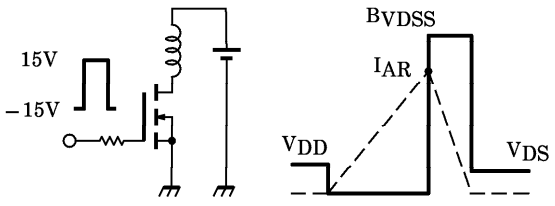


SAFE OPERATING AREA



$E_{AS} - T_{ch}$





TEST CIRCUIT WAVE FORM

Peak $I_{AR} = 1A$, $R_G = 25\Omega$
$V_{DD} = 50V$, $L = 56.7mH$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$